

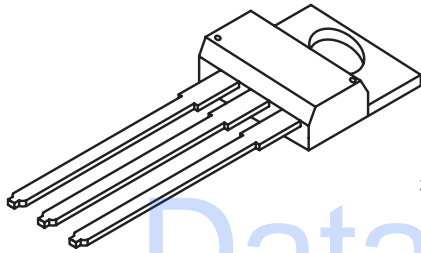


PART NO.

2N6292

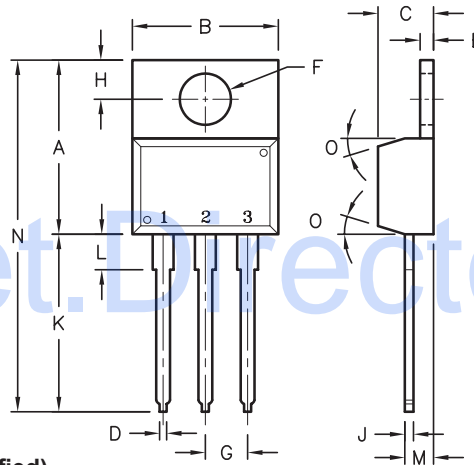
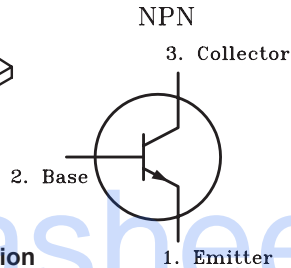
REVISIONS

ECN #	REV	DESCRIPTION	DRAWN	DATE	CHECKD	DATE	APPRVD	DATE
-	1.0	RELEASED	AB	08/05/12	ER	08/05/12	ER	08/05/12



Pin Configuration

1. Emitter
2. Base
3. Collector



Absolute Maximum Ratings

Collector-Base Voltage, V_{CB0}	70V
Collector-Emitter Voltage, V_{CEO}	80V
Emitter-Base Voltage, V_{EB0}	5V
Continuous Collector Current, I_C	7A
Base Current, I_B	3A
Total Device Dissipation (T C = +25°C), P_D	40W
Derate above 25°C	40mW / °C
Operating Junction Temperature Range, T_J	-65°C to +150°C
Storage Temperature Range, T_{STG}	-65°C to +150°C

Electrical Characteristics : (T_A = + 25°C unless otherwise Specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF Characteristics						
Collector-Emitter Breakdown Voltage (Note 1)	$V_{(BR)CEO}$	$I_C = 100mA, I_B = 0$	70	-	-	V
Collector Cut-Off Current	I_{CEX}	$V_{CE} = 80V, V_{EB(OFF)} = 1.5V$	-	-	100	μA
	I_{CEO}	$V_{CB} = 60V, I_B = 0$	-	-	1	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	-	-	1	mA
ON Characteristics						
DC Current Gain (Note 1)	h_{FE}	$V_{CE} = 4V, I_C = 2A$	30	-	150	-
		$V_{CE} = 4V, I_C = 7A$	2.3	-	-	-
Collector-Emitter Saturation Voltage (Note 1)	$V_{CE(SAT)}$	$I_C = 7A, I_B = 3A$	-	-	3.5	V
Base-Emitter On Voltage (Note 1)	$V_{BE(ON)}$	$I_C = 7A, V_{CE} = 4V$	-	-	3	V
Small-Signal Characteristics						
Current Gain-Bandwidth Product (Note 2)	f_T	$V_{CE} = 4V, I_C = 500mA, f = 1MHz$	4	-	-	MHz
Output Capacitance	C_{OBO}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	-	-	250	pF
Small-Signal Current Gain	h_{FE}	$V_{CE} = 4V, I_C = .5A, f = 50kHz$	20	-	-	-

Note 1: Pulse test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Note 2: f is defined as the frequency at which h extrapolates to unity.

Dimensions	Min.	Max.
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D	—	0.9
E	1.15	1.4
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J	—	0.56
K	12.7	14.73
L	2.8	4.07
M	2.03	2.92
N	—	31.24
O	DEF 7	

Part Number Table

Description	Part Number
Silicon T0-220 Plastic NPN Power Transistor	2N6292

www.element14.com
www.farnell.com
www.newark.com

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AB	08/05/12
CHECKED BY:	DATE:
ER	08/05/12
APPROVED BY:	DATE:
ER	08/05/12

DRAWING TITLE:			
Silicon T0220 Plastic NPN Power Transistor			
SIZE	DWG NO.	ELECTRONIC FILE	REV
A4	2N6292-01	2N6292-1	1.0
SCALE: NTS		U.O.M.: mm	SHEET: 1 of 1